

# isc N-Channel MOSFET Transistor

2SK2431

#### **DESCRIPTION**

- Drain Current I<sub>D</sub>= 3A@ T<sub>C</sub>=25 ℃
- · Drain Source Voltage-
  - : V<sub>DSS</sub>= 450V(Min)
- · Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

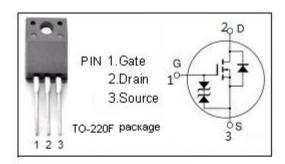
### **APPLICATIONS**

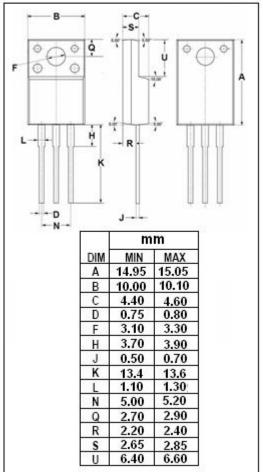
- Switching Regulators
- · DC-DC Converter,
- Motor Control



## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL               | ARAMETER                                  | VALUE   | UNIT       |
|----------------------|---|---------|------------|
| $V_{DSS}$            | Drain-Source Voltage (V <sub>GS</sub> =0) | 450     | ٧          |
| V <sub>GS</sub>      | Gate-Source Voltage                       | ±30     | V          |
| I <sub>D</sub>       | Drain Current-continuous@ TC=25℃          | 3       | Α          |
| I <sub>D(puls)</sub> | Pulsed Drain Current                      | 12      | А          |
| P <sub>tot</sub>     | Total Dissipation@T <sub>C</sub> =25℃     | 25      | W          |
| T <sub>j</sub>       | Max. Operating Junction Temperature       | 150     | $^{\circ}$ |
| T <sub>stg</sub>     | Storage Temperature Range                 | -55~150 | $^{\circ}$ |







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### • ELECTRICAL CHARACTERISTICS (Tc=25°C)

| SYMBOL               | PARAMETER                       | CONDITIONS   | MIN | TYPE | MAX | UNIT |
|----------------------|---------------------------------|--|-----|------|-----|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 10mA                     | 450 |      |     | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | V <sub>DS</sub> = 10V; I <sub>D</sub> =1mA                     | 2.0 |      | 3.0 | V    |
| V <sub>SD</sub>      | Diode Forward On-Voltage        | I <sub>S</sub> =3.0A ;V <sub>GS</sub> = 0                      |     | 0.9  |     | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> = 2A                     |     | 2.0  | 2.8 | Ω    |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±25V;V <sub>DS</sub> = 0                     |     |      | ±10 | μA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = 450V; V <sub>GS</sub> = 0                    |     |      | 250 | μA   |
| C <sub>iss</sub>     | Input Capacitance               | $V_{DS}$ =10V;<br>$V_{GS}$ =0V;<br>$f_T$ =1MHz                 |     | 330  |     | pF   |
| C <sub>rss</sub>     | Reverse Transfer Capacitance    |  |     | 15   |     |      |
| Coss                 | Output Capacitance              |  |     | 90   |     |      |
| tr                   | Rise Time                       | $V_{GS}$ =10 $V$ ;<br>$I_{D}$ =2 $A$ ;<br>$R_{L}$ =15 $\Omega$ |     | 20   |     |      |
| t <sub>d(on)</sub>   | Turn-on Delay Time              |  |     | 7    |     |      |
| t <sub>f</sub>       | Fall Time                       |  |     | 20   |     | ns   |
| $t_{d(off)}$         | Turn-off Delay Time             |  |     | 30   |     |      |

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